

WHAT IS CLAIMED IS:

1.           A semiconductor laser device comprising: a stem body having a reference surface; a heat radiation block which is provided on the reference surface of the stem body  
5       and which has a semiconductor laser chip mounted on a side face thereof; and a lead which extends through the stem body, wherein

              a portion of the lead protruding on a reference surface side is placed on one side surface side of the heat  
10       radiation block on which the semiconductor laser chip is mounted, and

              the semiconductor laser device further comprises a cover which is fixed to at least one of the heat radiation block and the stem body so as to surround the  
15       semiconductor laser chip and the portion of the lead protruding on the reference-surface side, in conjunction with the heat radiation block, and which is opened on at least one side of the cover that is a beam-output side of the semiconductor laser chip.

20       2.           The semiconductor laser device according to Claim 1, wherein

              the cover is made of a resin material.

3.           The semiconductor laser device according to Claim 1, wherein

a depth of the cover in the beam-output direction of the semiconductor laser chip is substantially equal to a depth of the heat radiation block.

4. The semiconductor laser device according to Claim  
5 1, wherein

the cover has a recessed portion for putting therein a resin for bonding the cover to the heat radiation block.

5. The semiconductor laser device according to Claim  
10 1, wherein

the heat radiation block has a recessed portion for putting therein a resin for bonding the cover to the heat radiation block.